MOSFET – Power, Single, P-Channel, SOT-23

-30 V, -1.95 A

NTR4502P, NVTR4502P

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max (Note 1)
−30 V	155 mΩ @ −10 V	−1.95 A
	240 mΩ @ −4.5 V	

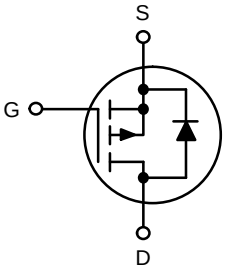
Features

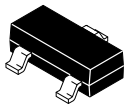
- Leading Planar Technology for Low Gate Charge/Fast Switching
- Low $R_{DS(ON)}$ for Low Conduction Losses
- SOT-23 Surface Mount for Small Footprint (3 x 3 mm)
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- DC to DC Conversion
- Load/Power Switch for Portables and Computing
- Motherboard, Notebooks, Camcorders, Digital Camera's, etc.
- Battery Charging Circuits

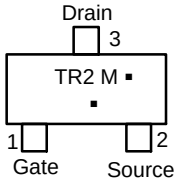
P-Channel MOSFET





SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM/ PIN ASSIGNMENT



TR2 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

* Date Code orientation and/or overbar may vary depending upon manufacturing location.

MAXIMUM RATINGS (T_J = 25 °C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	−30	V
Gate-to-Source Voltage			V_{GS}	±20	V
Drain Current (Note 1)	t < 10 s	T_A = 25 °C	I_D	−1.95	A
		T_A = 70 °C		−1.56	
Power Dissipation (Note 1)	t < 10 s		P_D	1.25	W
Continuous Drain Current (Note 1)	Steady State	T_A = 25 °C	I_D	−1.13	A
		T_A = 70 °C		−0.90	
Power Dissipation (Note 1)	Steady State		P_D	0.4	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−6.8	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−1.25	A
Lead Temperature for Soldering Purposes (1/8 in from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient − Steady State (Note 1)	$R_{\theta JA}$	300	°C/W
Junction-to-Ambient − t = 10 s (Note 1)	$R_{\theta JA}$	100	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).

ORDERING INFORMATION

Device	Package	Shipping†
NTR4502PT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NVTR4502PT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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Electrical Characteristics (T_J = 25 °C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −30 V	T_J = 25 °C			−1	μA
			T_J = 55 °C			−10	
Gate-to-Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−1.0		−3.0	V
Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = −10 V, I_D = −1.95 A			155	200	mΩ
		V_{GS} = −4.5 V, I_D = −1.5 A			240	350	
Forward Transconductance	g_{FS}	V_{DS} = −10 V, I_D=−1.25 A			3		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = −15 V			200		pF
Output Capacitance	C_{OSS}				80		
Reverse Transfer Capacitance	C_{RSS}				50		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −10 V, V_{DS} = −15 V; I_D = −1.95 A			6	10	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.3		
Gate-to-Source Charge	Q_{GS}				1		
Gate-to-Drain Charge	Q_{GD}				1.7		
SWITCHING CHARACTERISTICS (Note 4)							
Turn-On Delay Time	$t_{d(ON)}$	V_{GS} =−10 V, V_{DD} = −15 V, I_D = −1.95 A, R_G = 6 Ω			5.2	10	ns
Rise Time	t_r				12	20	
Turn-Off Delay Time	$t_{d(OFF)}$				19	35	
Fall Time	t_f				17.5	30	
DRAIN-SOURCE DIODE CHARACTERISTICS (Note 3)							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −1.25 A			−0.8	−1.2	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_{SD}/d_t = 100 A/μs, I_S = −1.25 A			23		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).
3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

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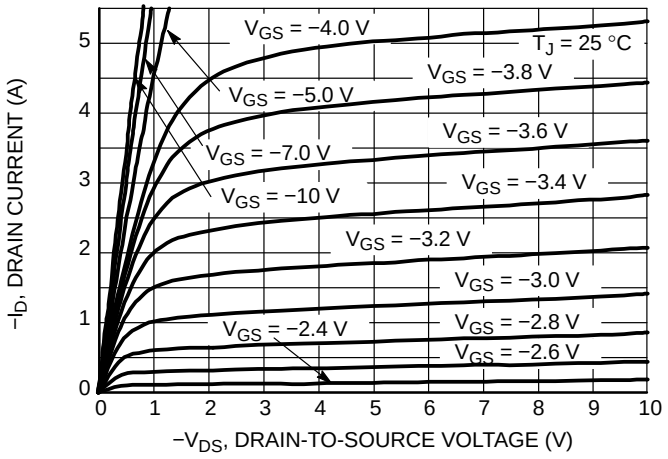


Figure 1. On-Region Characteristics

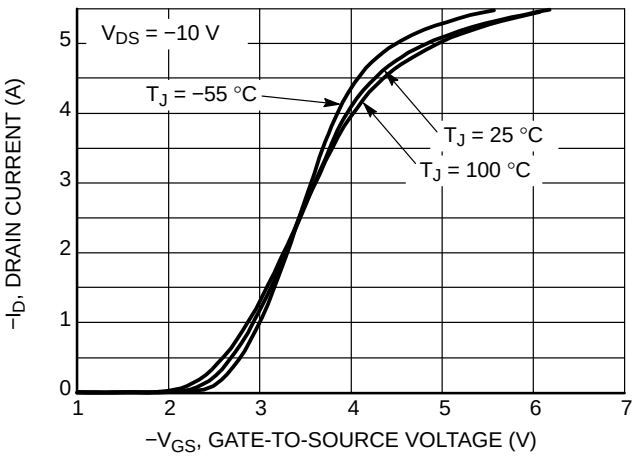


Figure 2. Transfer Characteristics

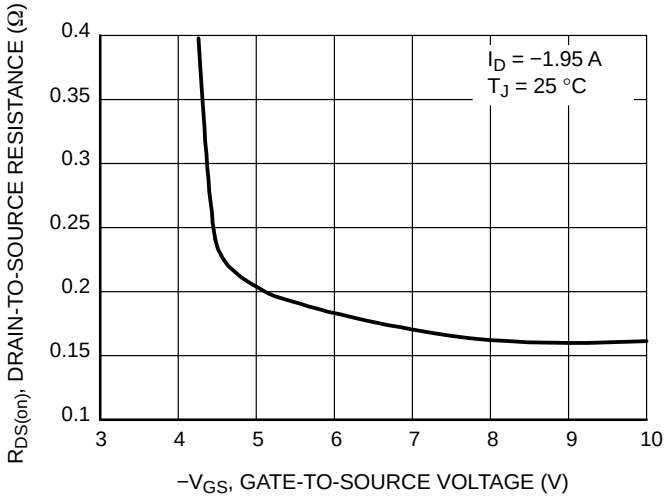


Figure 3. On-Resistance versus Gate-to-Source Voltage

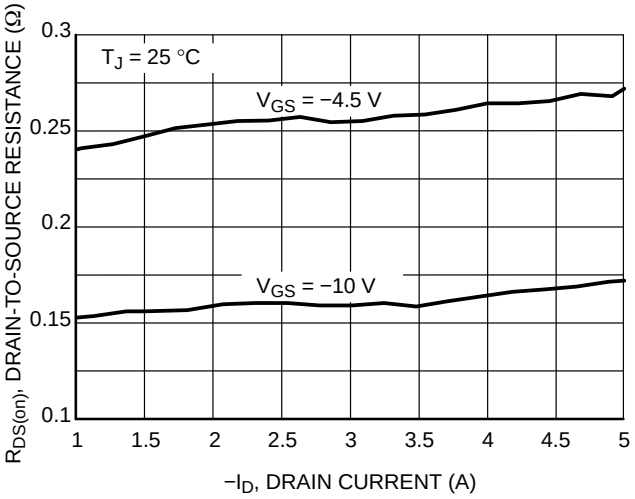


Figure 4. On-Resistance versus Drain Current and Gate Voltage

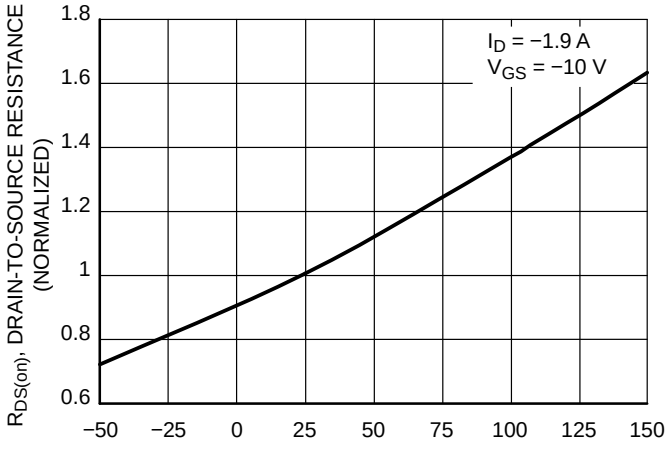


Figure 5. On-Resistance Variation with Temperature

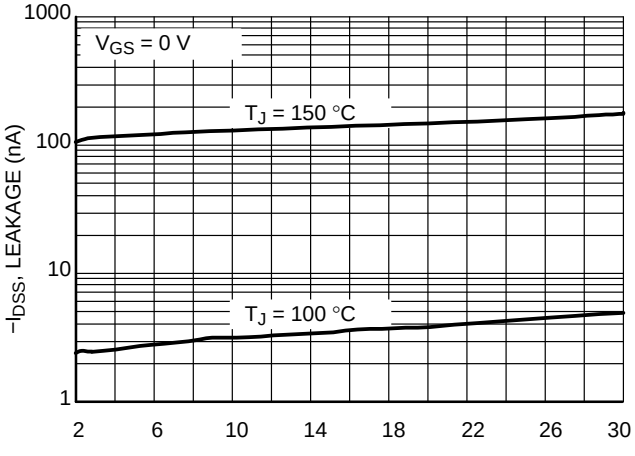


Figure 6. Drain-to-Source Leakage Current versus Voltage

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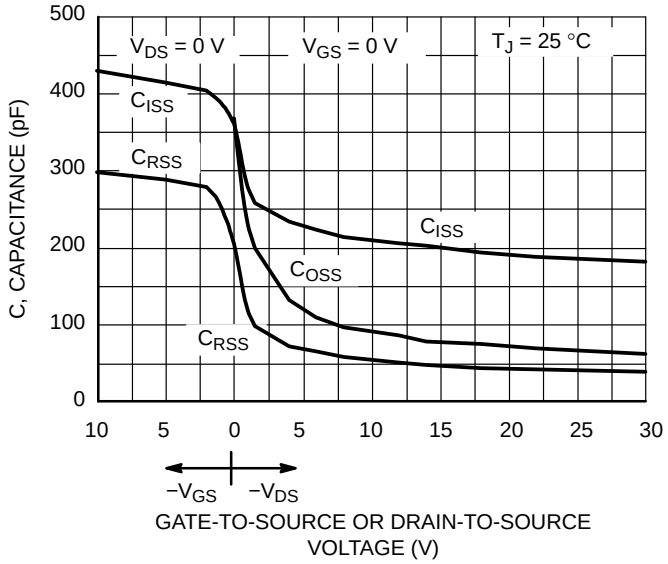


Figure 7. Capacitance Variation

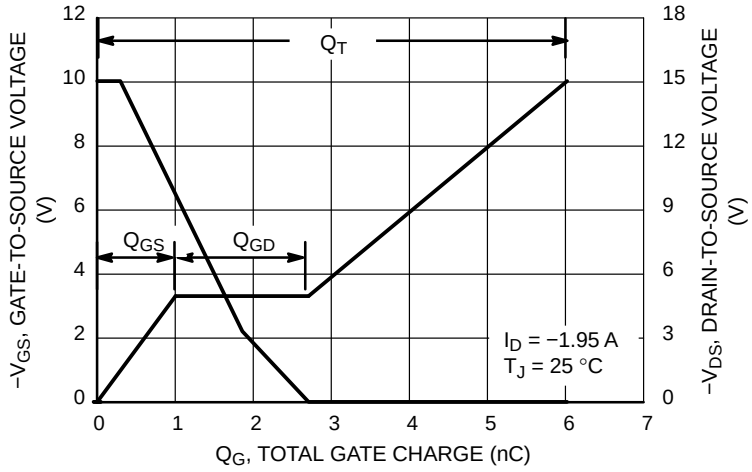


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

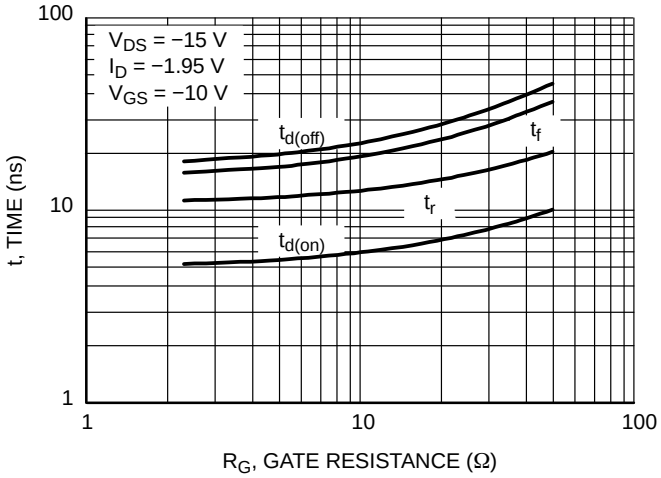


Figure 9. Resistive Switching Time Variation versus Gate Resistance

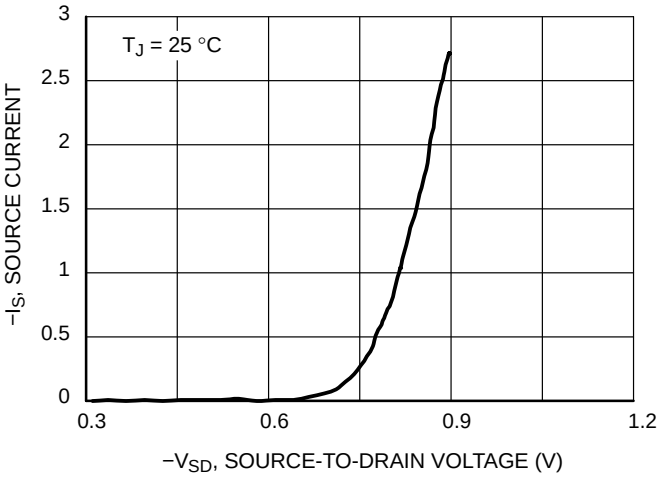


Figure 10. Diode Forward Voltage versus Current

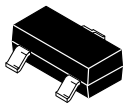
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REVISION HISTORY

Revision	Description of Changes	Date
7	Rebranded the document to **onsemi** format.	2/4/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

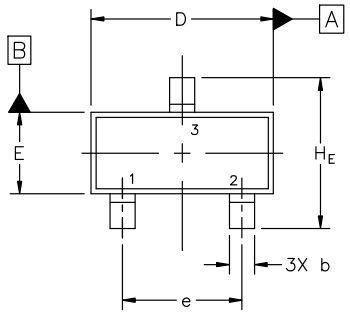
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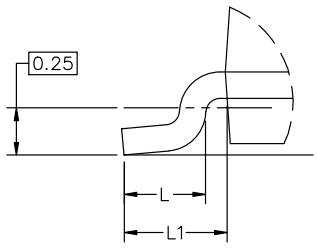
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

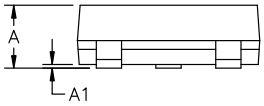
DATE 14 AUG 2024



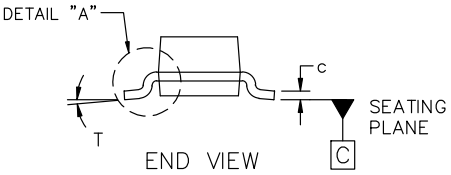
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

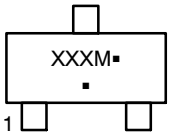


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

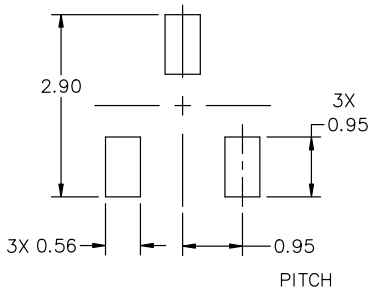
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**		**PAGE 1 OF 2**

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CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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